



No.5321

**2SC5265**

NPN Triple Diffused Planar Silicon Transistor

Inverter-controlled Lighting Applications

**Features**

- High breakdown voltage ( $V_{CBO} = 1200V$ ).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.

**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

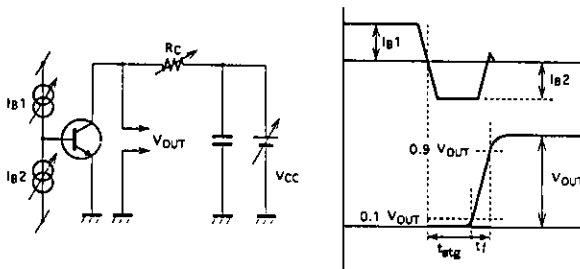
			unit
Collector-to-Base Voltage	$V_{CBO}$	1200	V
Collector-to-Emitter Voltage	$V_{CEO}$	600	V
Emitter-to-Base Voltage	$V_{EBO}$	9	V
Collector Current	$I_C$	4	A
Collector Current (Pulse)	$I_{CP}$	8	A
Collector Dissipation	$P_C$	2	W
		30	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

$T_c = 25^\circ C$

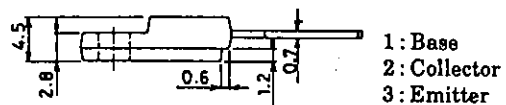
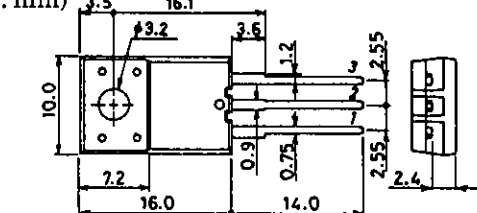
**Electrical Characteristics at  $T_a = 25^\circ C$**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 600V, I_E = 0$			10	$\mu A$
Collector Cutoff Current	$I_{CES}$	$V_{CE} = 1200V, R_{BE} = 0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100mA, I_B = 0$	600			V
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 9V, I_C = 0$			1.0	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 2.0A, I_B = 0.4A$			1.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 2.0A, I_B = 0.4A$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 0.3A$	30	40	50	
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 1.5A$	10			
Storage Time	$t_{stg}$	$I_C = 2.0A, I_{B1} = 0.4A, I_{B2} = -0.8A$			2.5	$\mu s$
Fall Time	$t_f$	$I_C = 2.0A, I_{B1} = 0.4A, I_{B2} = -0.8A$			0.15	$\mu s$

**Switching Time Test Circuit**



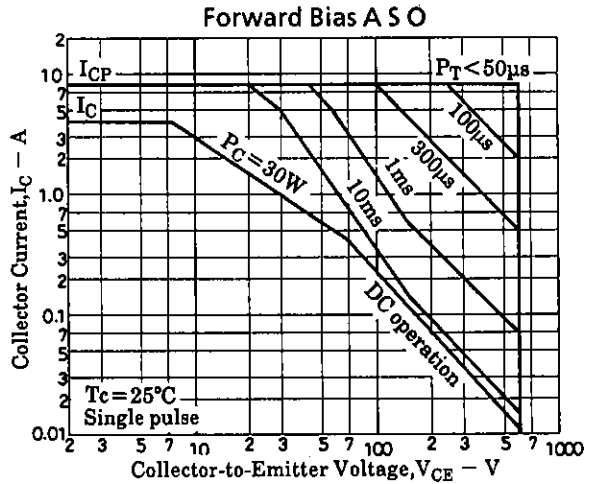
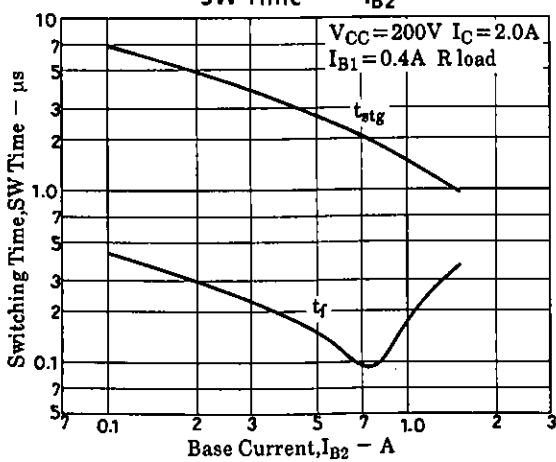
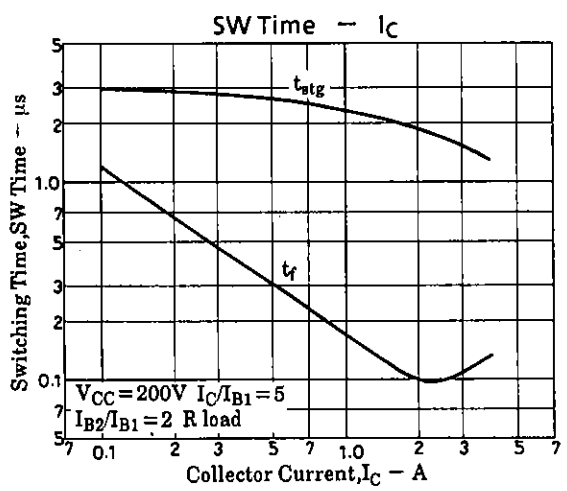
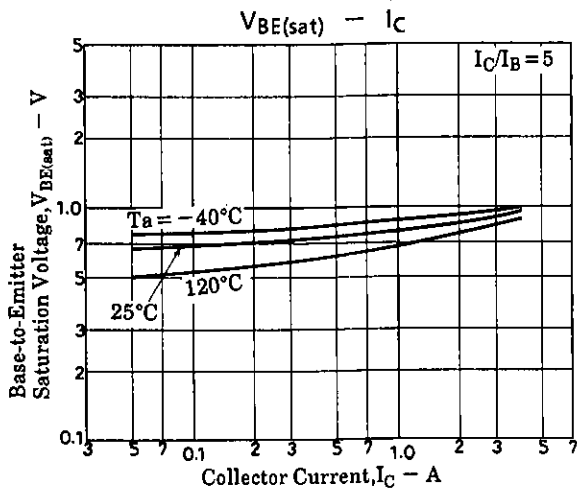
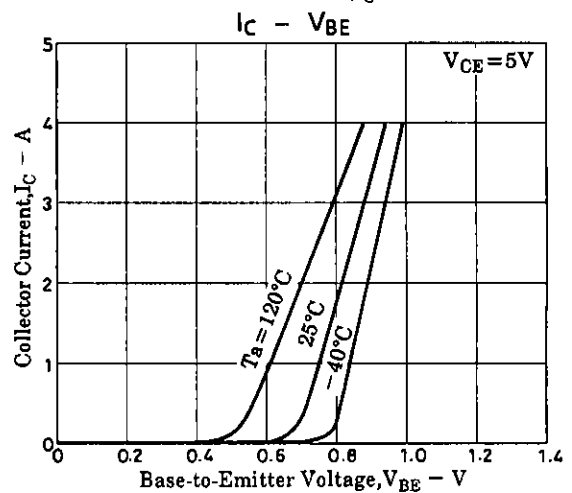
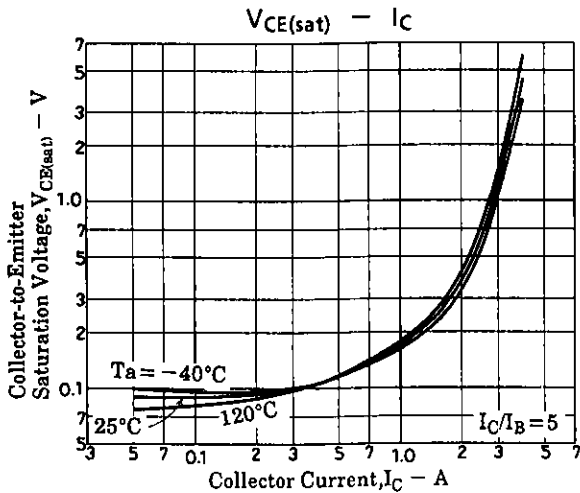
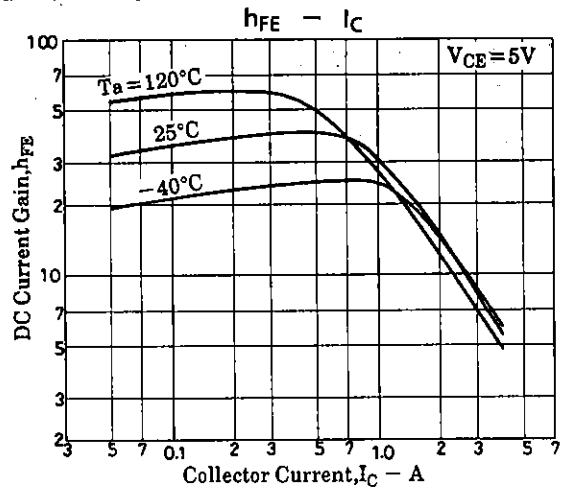
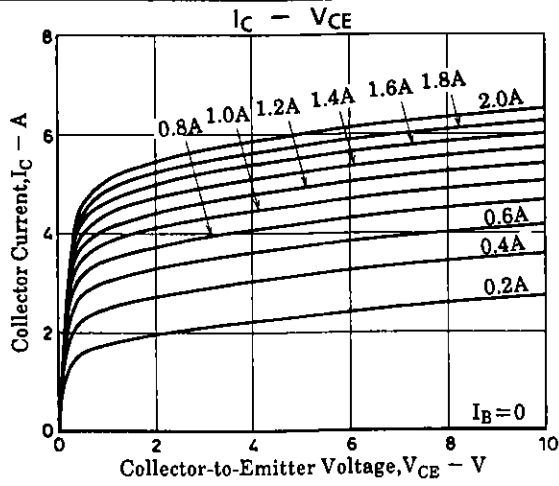
**Package Dimensions 2079B**  
(unit : mm)

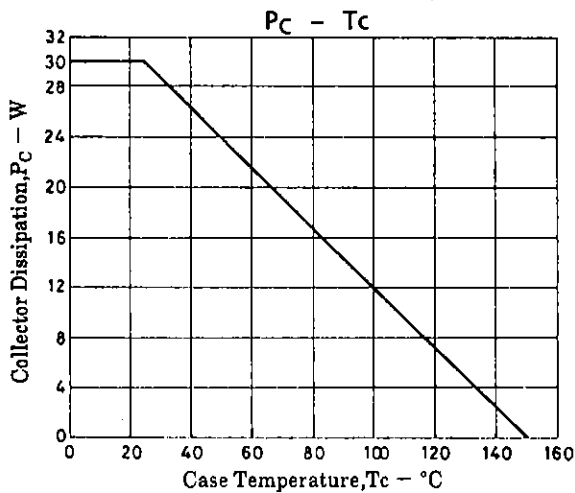
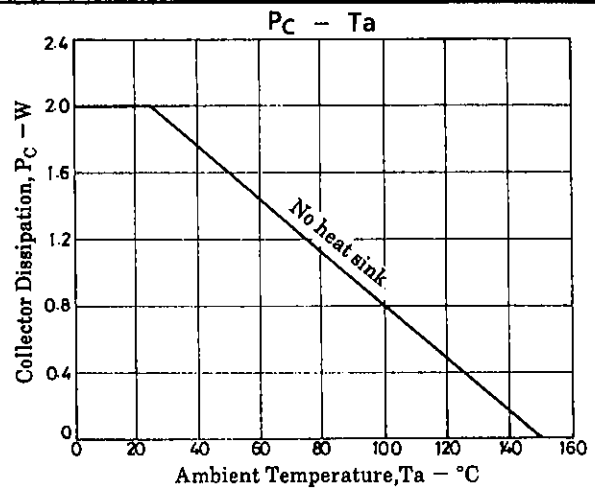
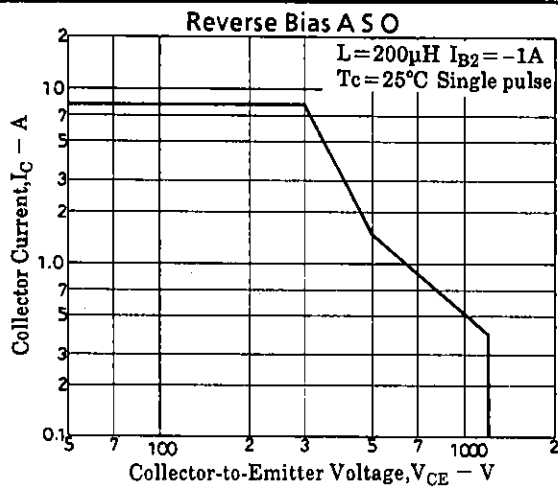


- 1 : Base
- 2 : Collector
- 3 : Emitter

SANYO : TO-220FI(LS)

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